Silicon PNP Power Transistors 2SA755

DESCRIPTION

·With TO-220 package
·Complement to type 2SC1419
·Note:Type 2SA754 with short pin

APPLICATIONS

·For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

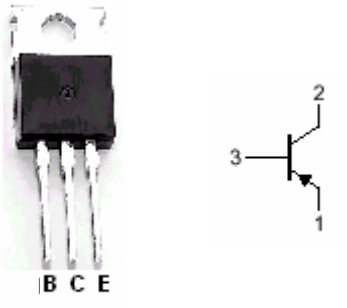

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-2	A
P_C	Collector power dissipation	T_C=25□	20	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ,R_{BE}=∞	-50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-5mA ,I_E=0	-50			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-5mA ,I_C=0	-4			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.5A; I_B=-0.15A			-1.3	V
V_{BE}	Base-emitter on voltage	I_C=-1A ; V_{CE}=-4V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-20V; I_E=0			-100	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-4V	35		200	
h_{FE-2}	DC current gain	I_C=-0.1A ; V_{CE}=-4V	35			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-4V		50		MHz

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200

PACKAGE OUTLINE

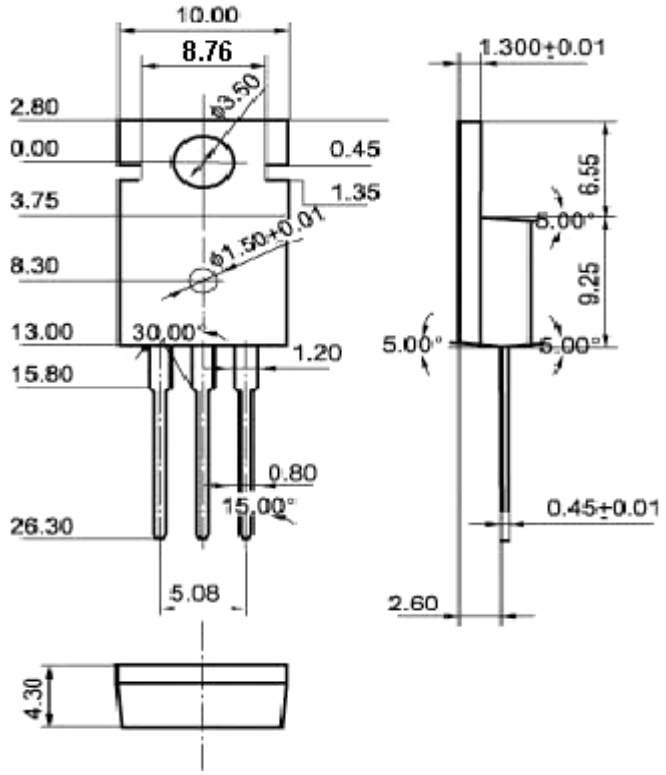

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)